



6P/2814

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: INOUE, et al.

Group Art Unit: 2814

Serial No.: 09/473,988

Examiner: DOAN, Theresa T.

Filed: December 29, 1999

P.T.O. Confirmation No.: 1714

For. SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

October 24, 2002

Sir:

In response to the Office Action dated July 29, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 8 as follows

8. (Five Times Amended) A semiconductor device comprising a semiconductor element formed on a semiconductor substrate, and a multilayer interconnection structure formed over said semiconductor element and electrically connected to said semiconductor element,

wherein said multilayered interconnection structure is an interconnection structure of at least two layers in which a conductive film or a lower interconnection layer and an upper interconnection layer formed on an insulating interlayer are electrically connected through a contact hole formed in said insulating interlayer,

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